

# **ISC Silicon NPN Power Transistor**

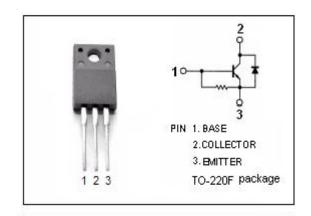
# **BU1508DX**

#### **DESCRIPTION**

- High Voltage
- · High Speed Switching
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

 Designed for use in horizontal deflection circuits of color TV receivers.

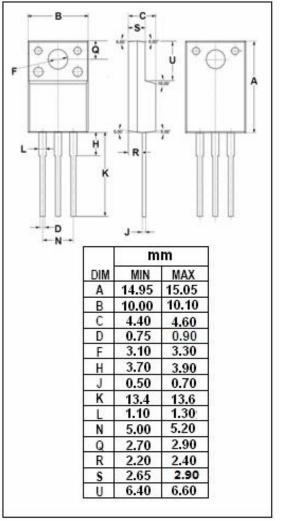


## ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
Vces	Collector-Base Voltage V <sub>BE</sub> = 0	1500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	700	V
V <sub>EBO</sub>	Emitter-Base Voltage	7.5	V
Ic	Collector Current-Continuous	8	Α
I <sub>CM</sub>	Collector Current-Peak	15	А
lΒ	Base Current-Continuous	4	Α
I <sub>BM</sub>	Base Current-peak	6	Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	35	W
Tj	Junction Temperature	150	${\mathbb C}$
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$

# THERMAL CHARACTERISTICS

SYMBOL	YMBOL PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	3.6	°C/W





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**BU1508DX** 

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
VCEO(SUS)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	700			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 600mA; I <sub>C</sub> = 0	7.5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 1.1A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 1.7A			1.3	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = V <sub>CES</sub> ; V <sub>BE</sub> = 0 V <sub>CE</sub> = V <sub>CES</sub> ; V <sub>BE</sub> = 0;T <sub>C</sub> =125°C			1.0 2.0	mA
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7.5V; I <sub>C</sub> = 0	140		390	
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		13		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4.5A ; V <sub>CE</sub> = 1V	4		7	
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 4.5A			2.0	V

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